

LME49726 High Current, Low Distortion, Rail-to-Rail Output Audio Operational Amplifier

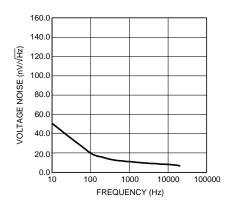
Check for Samples: LME49726

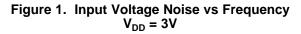
FEATURES

- Rail-to-Rail Output
- Easily Drives 2kΩ Loads to within 4mV of Each Power Supply Voltage Rail
- Optimized for Superior Audio Signal Fidelity
- Output Short Circuit Protection
- High Output Drive (>300mA)
- Available in VSSOP Exposed-DAP Package

KEY SPECIFICATIONS

- Power Supply Voltage Range: 2.5 to 5.5 V
- Quiescent Current per Amplifier at 5V: 0.7 mA (Typ)
- THD+N, $A_V = 1$, $f_{IN} = 1$ kHz, $R_L = 10$ k Ω :
 - (V_{OUT} = 3.5V_{P-P}, V_{DD} = 5.0V): 0.00008 % (Typ)
 - $(V_{OUT} = 1.5V_{P-P}, V_{DD} = 2.5V)$: 0.00002 % (Typ)
- Equivalent Input Noise (f = 10k): 8.3 nV/\/Hz (Typ)
- Slew Rate: ±3.7 V/µs (Typ)
- Gain Bandwidth Product: 6.25 MHz (Typ)
- Open Loop Gain (R_L = 10kΩ): 120 dB (Typ)
- Input Bias Current: 0.2 pA (Typ)
- Input Offset Voltage: 0.5 mV (Typ)
- PSRR (DC): 104 dB (Typ)





APPLICATIONS

- Portable Audio Amplification
- Preamplifiers and Multimedia
- Equalization and Crossover Networks
- Line Drivers and Receivers
- Active Filters
- DAC I–V Converter Gain Stage
- ADC Front-End Signal Conditioning

DESCRIPTION

The LME49726 is a low distortion, low noise rail-torail output audio operational amplifier optimized and fully specified for high performance, high fidelity applications. The LME49726 delivers superior audio amplification for outstanding signal audio performance. The LME49726 has a very low THD+N to easily satisfy demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49726 provides output current greater than 300mA at 5V. Further, dynamic range is maximized by an output that drives 2kΩ loads to within 4mV of either power supply voltage.

The LME49726 has a supply range of 2.5V to 5.5V. Over this supply range the LME49726's input circuitry maintains excellent common-mode and power supply rejection, as well as maintaining its low input bias current. The LME49726 is unity gain stable.

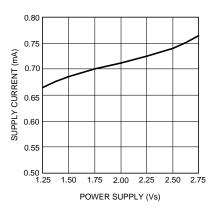


Figure 2. Supply Current vs Supply Voltage per Amplifier, $R_L = No Load$, $A_V = -1$

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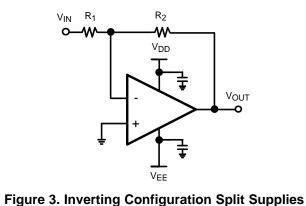
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Typical Connections



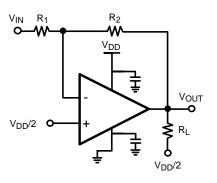


Figure 4. Inverting Configuration Single Supplies

Connection Diagram

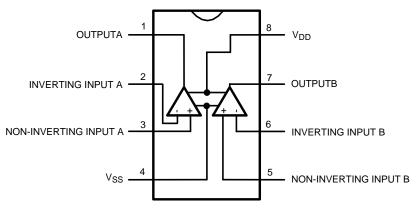


Figure 5. See Package Number DGN0008A

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾⁽²⁾⁽³⁾

Power Supply Voltage	$V_{S} = V_{SS} - V_{DD}$	6V
Storage Temperature		-65°C to 150°C
Input Voltage		$(V_{SS}) - 0.7V$ to $(V_{DD}) + 0.7V$
Output Short Circuit ⁽⁴⁾		Continuous
Power Dissipation		Internally Limited
ESD Rating ⁽⁵⁾		2000V
ESD Rating ⁽⁶⁾		200V
Junction Temperature		150°C
Thermal Resistance	θ _{JA} (DGN0008A)	72°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified.

(2) The Electrical Characteristics tables list specifications under the listed Recommended Operating Conditions except as otherwise modified or specified by the Electrical Characteristics Conditions and/or Notes. Typical specifications are estimations only and are not ensured.

(3) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

(4) The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX}, θ_{JA}, and the ambient temperature, T_A. The maximum allowable power dissipation is P_{DMAX} = (T_{JMAX} - T_A) / θ_{JA} or the number given in Absolute Maximum Ratings, whichever is lower.

(5) Human body model, applicable std. JESD22-A114C.

(6) Machine model, applicable std. JESD22-A115-A.

OPERATING RATINGS⁽¹⁾

Temperature Range	$T_{MIN} \le T_A \le T_{MAX}$	-40°C ≤ T _A ≤ 125°C
Supply Voltage Range		2.5V ≤ V _S ≤ 5.5V

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. All voltages are measured with respect to the ground pin, unless otherwise specified. SNAS432C-NOVEMBER 2008-REVISED APRIL 2013

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STRUMENTS

EXAS

ELECTRICAL CHARACTERISTICS ($V_{DD} = 5.0V$ and $V_{DD} = 2.5V$)

The following specifications apply for the circuit shown in Figure 1. $V_{DD} = 5.0V$ and $V_{DD} = 2.5V$, $V_{SS} = 0.0V$, $V_{CM} = V_{DD/2}$, $R_L = 10k\Omega$, $C_{LOAD} = 20pF$, $f_{IN} = 1kHz$, BW = 20-20kHz, and $T_A = 25^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Conditions	LME4	Units	
Symbol	Parameter	Conditions	Typical ⁽¹⁾	Limit ⁽²⁾	(Limits)
		$ \begin{array}{l} A_V = -1, V_{OUT} = 3.5 V_{p\text{-}p}, V_{DD} = 5 V \\ R_L = 600 \Omega \\ R_L = 2 k \Omega \\ R_L = 10 k \Omega \end{array} $	0.0008 0.0002 0.00008		% % %
THD+N Total Harmonic Distortion + Noise			0.001 0.0008 0.0002		% % %
GBWP	Gain Bandwidth Product		6.25	5.0	MHz (min
SR	Slew Rate	$A_V = +1, R_L = 10k\Omega$	3.7	2.5	V/µs (min)
t _s	Settling time	A _V = 1V step 0.1% error range 0.001% error range	800 1.2		ns µs
e _N	Equivalent Input Noise Voltage	f _{BW} = 20Hz to 20kHz (A-weighted)	0.7	1.25	μV _{RMS} (max)
		f = 10kHz	8.3		nVI√Hz
e _N Equivalent	Equivalent Input Noise Density	f = 1kHz	10		nV / √Hz
		f = 100Hz	24		nV / √Hz
I _N	Current Noise Density	f = 1kHz	0.75		pA / √Hz
V _{OS}	Input Offset Voltage	$V_{IN} = V_{DD/2}, V_O = V_{DD/2}, A_V = 1$	0.5	2.25	mV (max)
ΔV _{OS} /ΔTemp	Average Input Offset Voltage Drift vs Temperature	$40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$	1.2		µV/°C
PSRR	Power Supply Rejection Ratio	2.5 to 5.5V, $V_{CM} = 0$, $V_{DD}/2$	104	85	dB (min)
ISO _{CH-CH}	Channel-to-Channel Isolation	f _{IN} = 1kHz	94		dB
I _B	Input Bias Current	$V_{CM} = V_{DD}/2$	±0.2		pА
ΔI _{OS} /ΔTemp	Input Bias Current Drift vs Temperature	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le 85^{\circ}\text{C}$	35		nA/°C
l _{os}	Input Offset Current	$V_{CM} = V_{DD}/2$	±0.2		pА
V _{IN-CM}	Common-Mode Input Voltage Range			V _{DD} 1.6 V _{SS} +0.1	V (min)
CMRR	Common Mode Rejection Ratio	$0.1V < V_{DD} - 1.6V$	95	80	dB (min)
1/f	1/f Corner Frequency		2		kHz
A _{VOL}	Open-Loop Voltage Gain	$V_{OUT} = V_{DD}/2$	120	100	dB (min)
Manager	Maximum Output Voltage Swing	$R_L = 2k\Omega$ to $V_{DD}/2$	V _{DD} -0.004 V _{SS} +0.004		V (min) V (max)
Voutswing	maximum Oupur voltage Swing	$R_L = 16\Omega$ to $V_{DD}/2$	V _{DD} –0.33 V _{SS} +0.33		V (min) V (max)
	Output Current	$V_{OUT} = 5V, V_{DD} = 5V$	350		mA
IOUT		$V_{OUT} = 2.5V, V_{DD} = 2.5V$	160		mA
	Quiescent Current per Amplifier	$I_{OUT} = 0mA, V_{DD} = 5V$	0.7	1.1	mA (max)
I _S	Quescent ourient per Ampliner	$I_{OUT} = 0mA$, $V_{DD} = 2.5V$	0.64	1.0	mA (max)

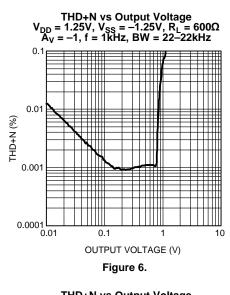
(1) Typical values represent most likely parametric norms at T_A = +25°C, and at the Recommended Operation Conditions at the time of product characterization and are not ensured. Datasheet min/max specification limits are specified by test or statistical analysis.

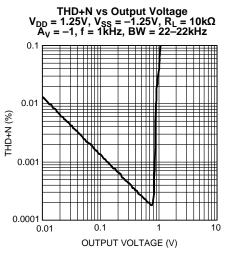
(2)



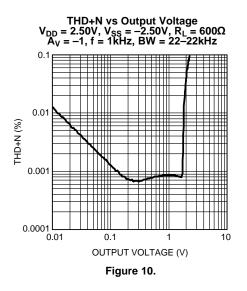
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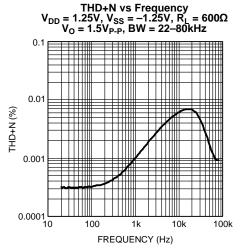
TYPICAL PERFORMANCE CHARACTERISTICS



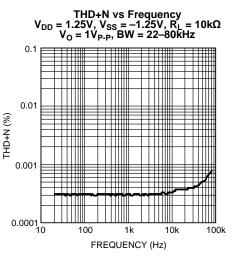




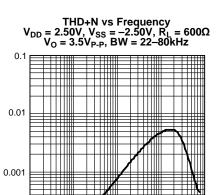


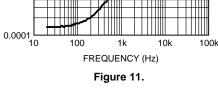












THD+N (%)



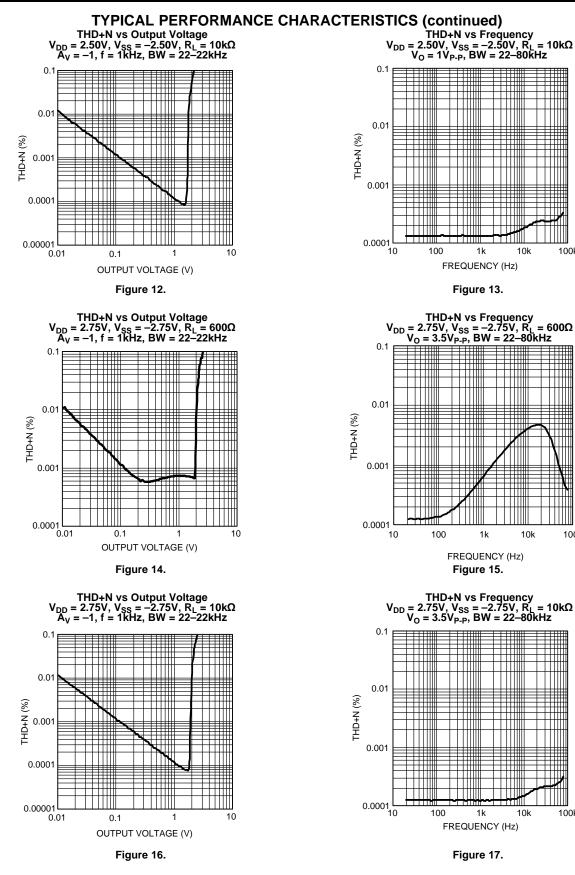
100k

100k

100k

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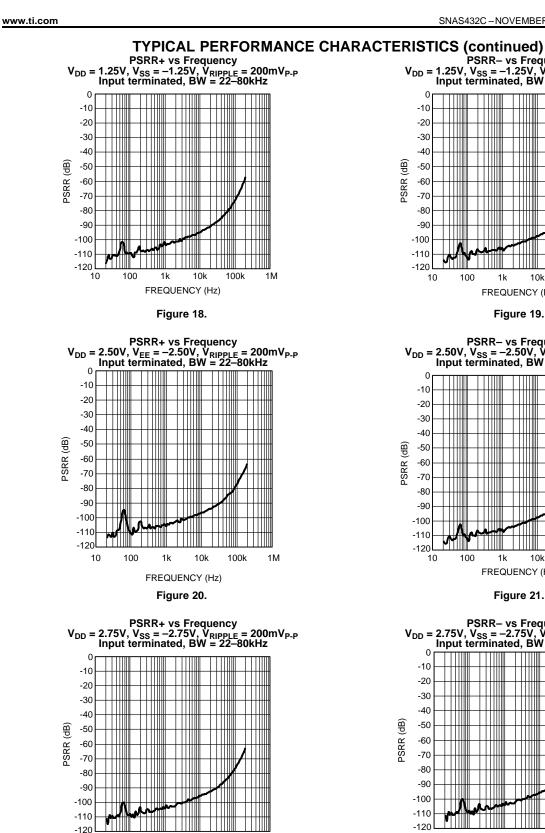
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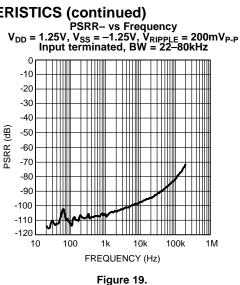


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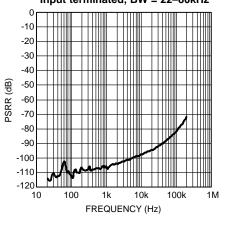


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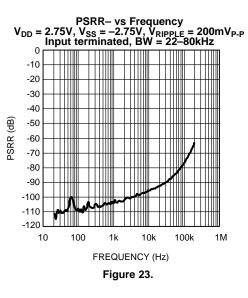




 $\label{eq:VDD} \begin{array}{l} \text{PSRR-vs Frequency} \\ \text{V}_{\text{DD}} = 2.50\text{V}, \ \text{V}_{\text{SS}} = -2.50\text{V}, \ \text{V}_{\text{RIPPLE}} = 200\text{mV}_{\text{P-P}} \\ \text{Input terminated, BW} = 22\text{--80kHz} \end{array}$







100

1k

FREQUENCY (Hz)

Figure 22.

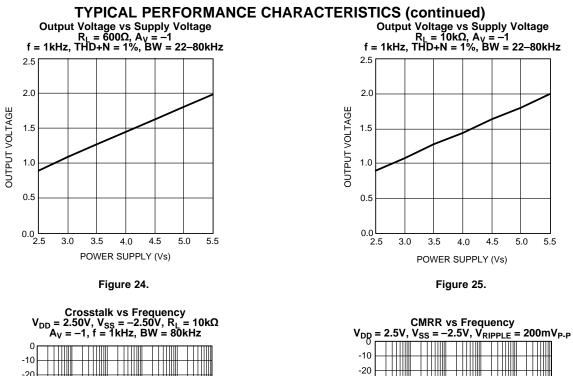
10k

100k

1M

10

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-30

-40

-70

-80

-90

-100

-110

-120

10

1k

FREQUENCY (Hz)

Figure 27.

10k

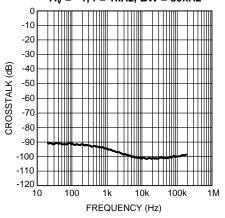
100k

1M

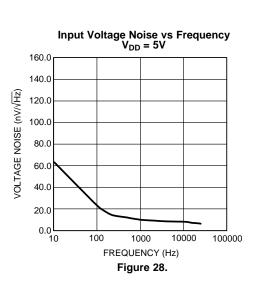
100

(qB) -50

CMRR (-60









APPLICATION INFORMATION

DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49726 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution. however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49726's low residual is an input referred internal error. As shown in Figure 29, adding the 10Ω resistor connected between athe amplifier's inverting and non-inverting inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 29.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so, produces distortion components that are within measurement equipment capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.

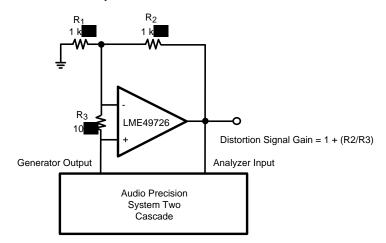


Figure 29. THD+N and IMD Distortion Test Circuit

OPERATING RATINGS AND BASIC DESIGN GUIDELINES

The LME49726 has a supply voltage range from +2.5V to +5.5V single supply or ±1.25 to ±2.75V dual supply.

Bypassed capacitors for the supplies should be placed as close to the amplifier as possible. This will help minimize any inductance between the power supply and the supply pins. In addition to a 10μ F capacitor, a 0.1μ F capacitor is also recommended in CMOS amplifiers.

The amplifier's inputs lead lengths should also be as short as possible. If the op amp does not have a bypass capacitor, it may oscillate.

BASIC AMPLIFIER CONFIGURATIONS

The LME49726 may be operated with either a single supply or dual supplies. Figure 2 shows the typical connection for a single supply inverting amplifier. The output voltage for a single supply amplifier will be centered around the common-mode voltage, V_{CM} . Note, the voltage applied to the V_{CM} insures the output stays above ground. Typically, the V_{CM} should be equal to $V_{DD}/2$. This is done by putting a resistor divider circuit at this node, see Figure 30.



NSTRUMENTS

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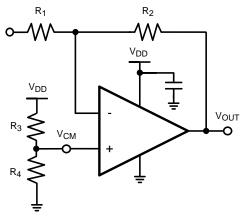


Figure 30. Single Supply Inverting Op Amp

Figure 31 shows the typical connection for a dual supply inverting amplifier. The output voltage is centered on zero.

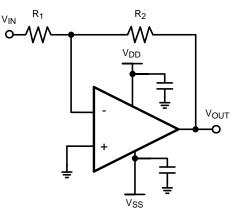


Figure 31. Dual Supply Inverting Configuration

Figure 32 shows the typical connection for the Buffer Amplifier or also called a Voltage Follower. The Buffer is a unity gain stable amplifier.

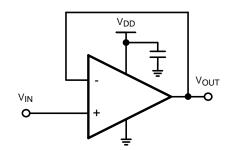


Figure 32. Unity-Gain Buffer Configuration



Typical Applications

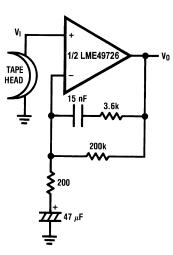
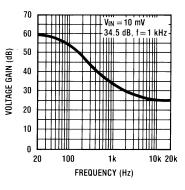
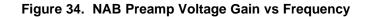


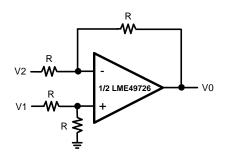


Figure 33. NAB Preamp

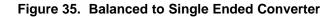


 $\begin{array}{l} A_V = 34.5 \\ F = 1 \ kHz \\ E_n = 0.38 \ \mu V \\ A \ Weighted \end{array}$





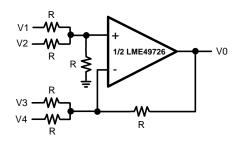
 $V_0 = V1 - V2$





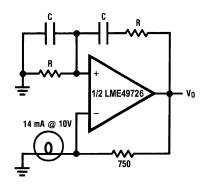
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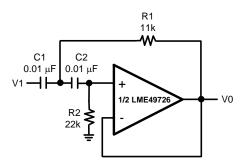
$$V_0 = V1 + V2 - V3 - V4$$

Figure 36. Adder/Subtracter









 $\text{if } C1 \ = \ C2 \ = \ C$

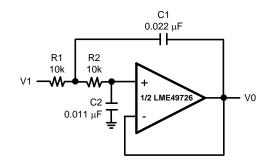
$$R1 = \frac{\sqrt{2}}{2\omega_0 C}$$
$$R2 = 2 \cdot R1$$

Illustration is $f_0 = 1 \text{ kHz}$

Figure 38. Second Order High Pass Filter (Butterworth)



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if R1 = R2 = R
C1 =
$$\frac{\sqrt{2}}{\omega_0 R}$$

C2 = $\frac{C1}{2}$

Illustration is $f_0 = 1 \text{ kHz}$



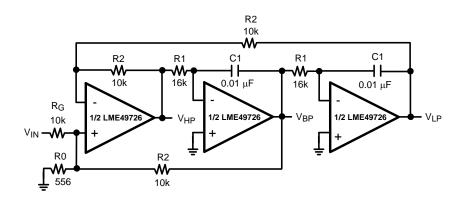


Figure 40. State Variable Filter

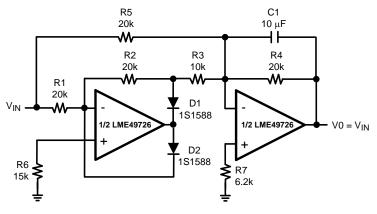
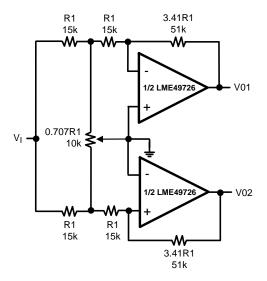


Figure 41. AC/DC Converter

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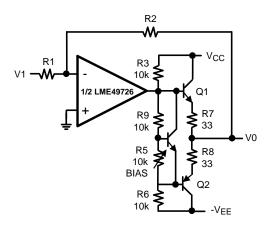
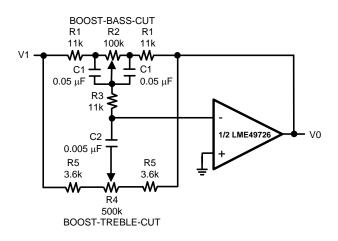


Figure 43. Line Driver



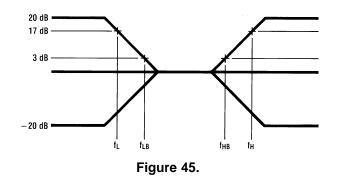
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$$\begin{split} \mathfrak{f}_L &= \frac{1}{2\pi R2C1}, \mathfrak{f}_{LB} = \frac{1}{2\pi R1C1} \\ \mathfrak{f}_H &= \frac{1}{2\pi R5C2}, \mathfrak{f}_{HB} = \frac{1}{2\pi (R1 + R5 + 2R3)C2} \\ Illustration is: \\ \mathfrak{f}_L &= 32 \ Hz, \ \mathfrak{f}_{LB} = 320 \ Hz \\ \mathfrak{f}_H &= 11 \ \text{kHz}, \ \mathfrak{f}_{HB} = 1.1 \ \text{kHz} \end{split}$$







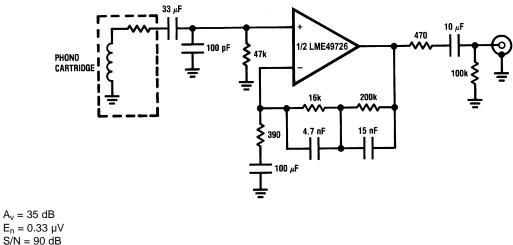
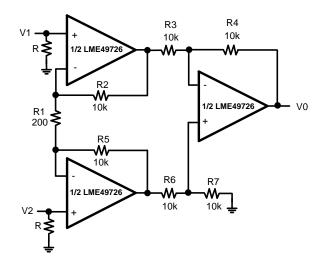


Figure 46.

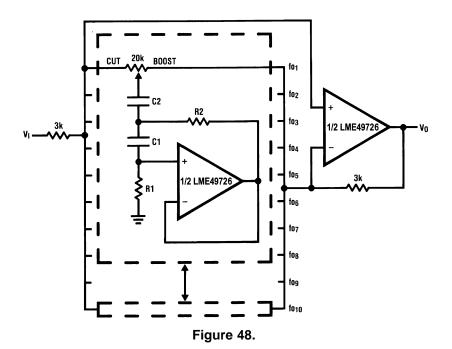


 $\begin{array}{ll} \text{If } \texttt{R2} = \texttt{R5}, \texttt{R3} = \texttt{R6}, \texttt{R4} = \texttt{R7} \\ \texttt{V0} = \left(1 + \frac{2\texttt{R2}}{\texttt{R1}}\right) \frac{\texttt{R4}}{\texttt{R3}}(\texttt{V2} - \texttt{V1}) \\ \text{Illustration is:} \\ \texttt{V0} = \texttt{101}(\texttt{V2} - \texttt{V1}) \end{array}$





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fo (Hz)	C ₁	C ₂	R ₁	R ₂
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.015µF 0.82µF		470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

LME49726 Bill of Materials

Description	Designator	Part Number	Manufacturer	Quantity/Brd
Ceramic Capacitor 0.1uF, 10%, 50V 0805 SMD	C1, C2, C5–C8	08055C104KAT2A	AVX	2
Tantalum Capacitor 2.2uF,10%, 20V, A-size	C9, C11	T491A225K020AT	Kemet	Not Stuff
Tantalum Capacitor 10uF,10%, 20V, B-size	C3, C4 T491B106K020AT		Kemet	2
Resistor 0Ω, 1/8W 1% 0805 SMD	R1, R4, R6, R9, R13, R14	CRCW08050000Z0EA	Vishay	6
Header, 2-Pin	JP1, JP2, JP3, JP4	HDR1X2	Header 2	4
Header, 3-Pin	JP5	HDR1X3	Header 3	1
Resistor 10kΩ, 1/8W 1% 0805 SMD	R2, R3, R7, R8	CRCW080510K0FKEA	Vishay	4
Dual Rail-to-Rail Op Amp	U1	LME49726	Texas Instruments	1
Resistor 100meg/open 1/8W 0805 SMD	R5, R10, R11, R12	OPEN N/A	N/A	0

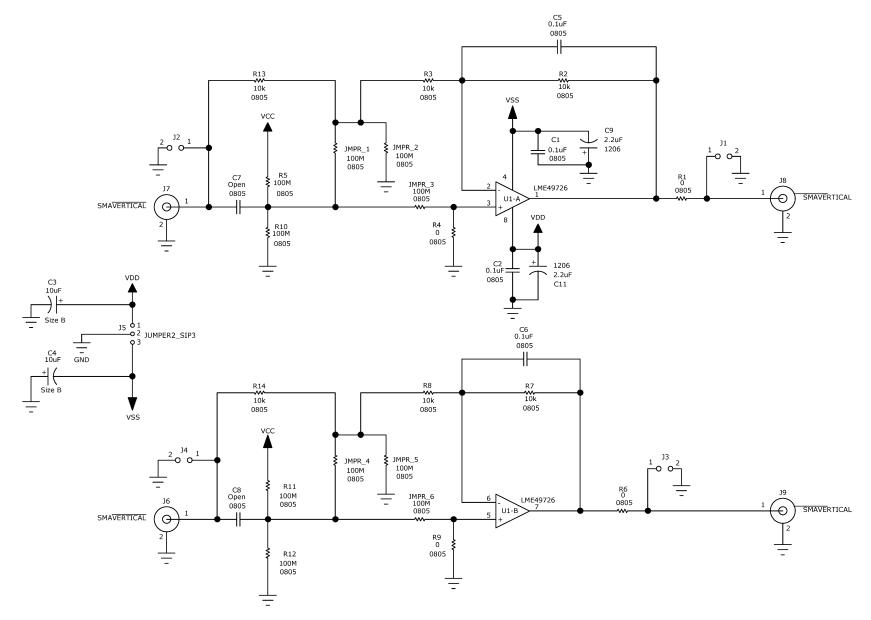
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LME49726



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LME49726 Board Circuit





SNAS432C - NOVEMBER 2008 - REVISED APRIL 2013

LME49726 Demo Board Views

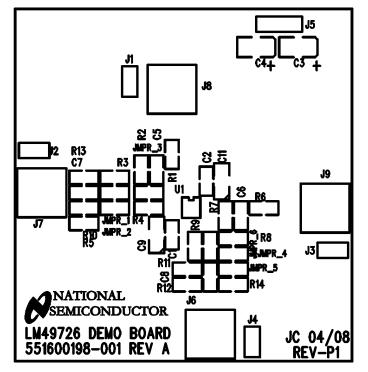


Figure 49. Top Silkscreen

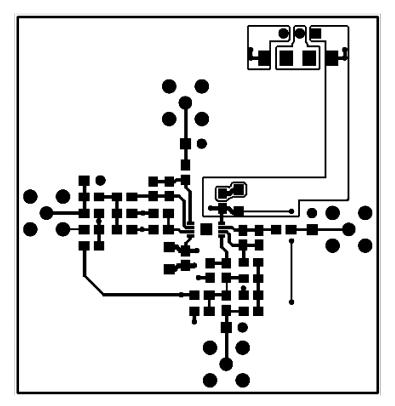


Figure 50. Top Layer



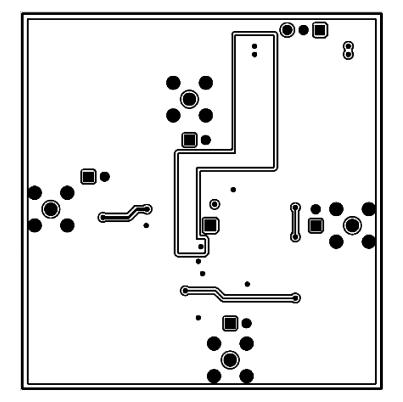


Figure 51. Bottom Layer



SNAS432C - NOVEMBER 2008 - REVISED APRIL 2013

REVISION HISTORY

Rev	Date	Description
1.0	11/05/08	Initial release.
1.01	05/25/10	Increased Operating Temperature Range.
1.02	07/14/11	Added curves 30038602 and 03 and input text edits.
1.03	07/19/11	Re-released the D/S to the WEB after adding curves 30038602 and 03 .
С	04/04/13	Changed layout of National Data Sheet to TI format.



6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LME49726MY/NOPB	ACTIVE	HVSSOP	DGN	8	1000	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 85	ZA3	Samples
LME49726MYX/NOPB	ACTIVE	HVSSOP	DGN	8	3500	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 85	ZA3	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

6-Feb-2020

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LME49726MY/NOPB	HVSSOP	DGN	8	1000	178.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LME49726MYX/NOPB	HVSSOP	DGN	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

6-Sep-2019



*All dimensions are nominal

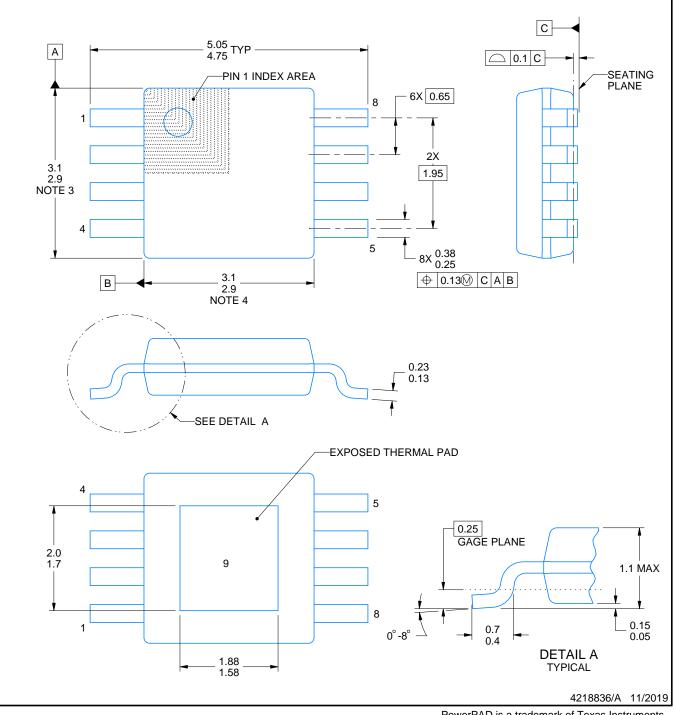
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LME49726MY/NOPB	HVSSOP	DGN	8	1000	210.0	185.0	35.0
LME49726MYX/NOPB	HVSSOP	DGN	8	3500	367.0	367.0	35.0

PACKAGE OUTLINE

DGN0008A

PowerPAD[™] VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.

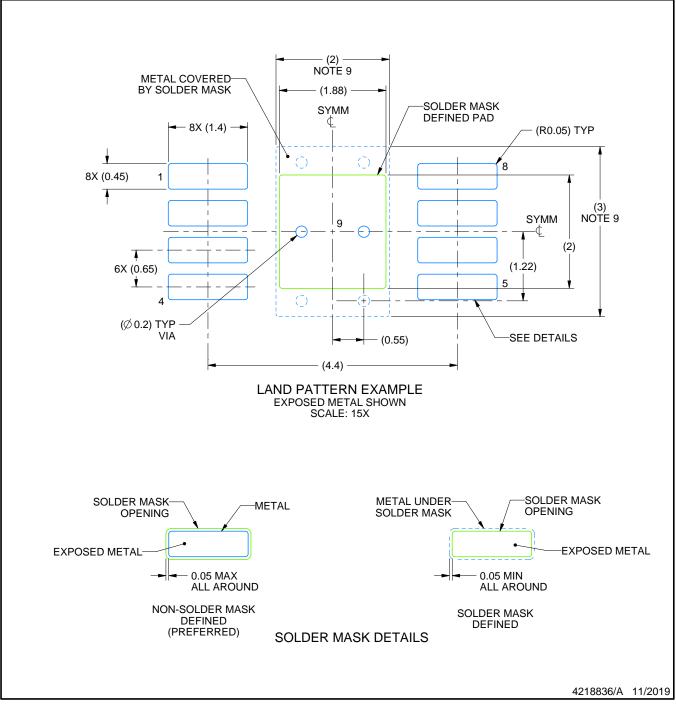


DGN0008A

EXAMPLE BOARD LAYOUT

PowerPAD[™] VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown
- on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.

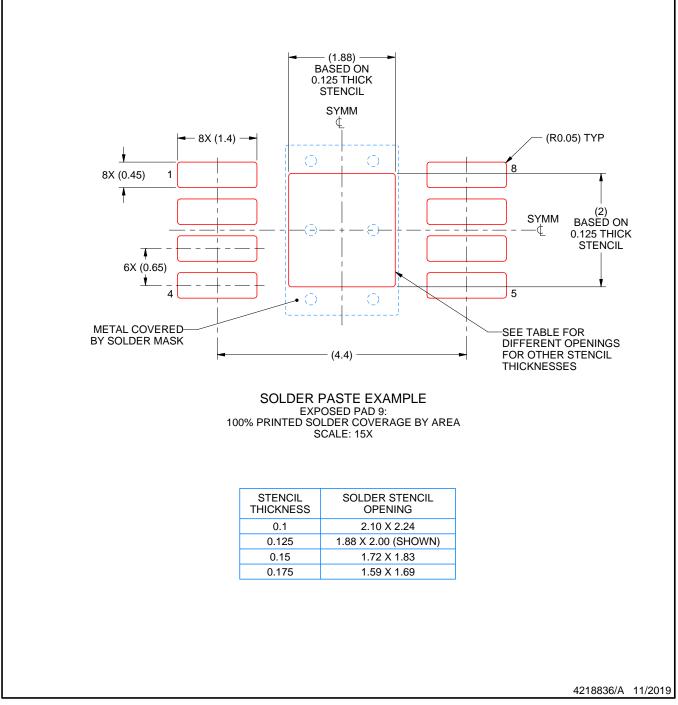


DGN0008A

EXAMPLE STENCIL DESIGN

PowerPAD[™] VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 10. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 11. Board assembly site may have different recommendations for stencil design.



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